Unit in mm

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2SC2510A

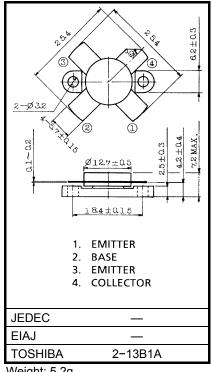
2~30MHz SSB LINEAR POWER AMPLIFIER APPLICATIONS (28V SUPPLY VOLTAGE USE)

Specified 28V, 28MHz Characteristics

Output Power $: Po = 150W_{PEP} (Min.)$ Power Gain : Gp = 12.2dB (Min.)Collector Efficiency $: \eta_C = 35\% \text{ (Min.)}$ Intermodulation Distortion: IMD = -30dB (Max.)

ABSOLUTE MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V _{CES}	60	٧
Collector-Emitter Voltage	V _{CEO}	35	٧
Emitter-Base Voltage	V _{EBO}	4	٧
Collector Current	IC	20	Α
Collector Power Dissipation	PC	250	W
Junction Temperature	Tj	175	°C
Storage Temperature Range	T _{stg}	-65~175	°C

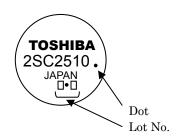


Weight: 5.2g

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

MARKING

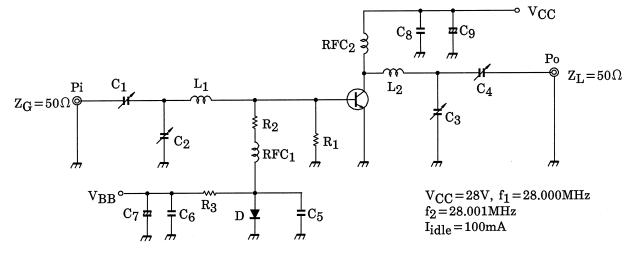


ELECTRICAL CHARACTERISTICS (Tc = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C = 100mA, I _B = 0	35	_	_	V
Collector-Emitter Breakdown Voltage	V (BR) CES	I _C = 100mA, V _{EB} = 0	55	_	_	V
Emitter-Base Breakdown Voltage	V (BR) EBO	I _E = 1mA, I _C = 0	4	_	_	٧
DC Current Gain	h _{FE}	V _{CE} = 5V, I _C = 10A *	10	_	_	
Collector Output Capacitance	C _{ob}	V _{CB} = 28V, I _E = 0 f = 1MHz	_	450	600	pF
Power Gain	Gp	$V_{CC} = 28V, f_1 = 28.000MHz,$ $f_2 = 28.001MHz$ $I_{idle} = 100mA$ $P_0 = 150W_{PEP}$ (Fig.)	12.2	13.3	_	dB
Input Power	Pi		_	7	9	W _{PEP}
Collector Efficiency	ηc		35	_	_	%
Intermodulation Distortion	IMD		_	_	-30	dB
Series Equivalent Input Impedance	Z _{in}	$V_{CC} = 28V, f_1 = 28.000MHz,$	_	1.4 -j0.9	_	Ω
Series Equivalent Output Impedance	Z _{out}	f ₂ = 28.001MHz, Po = 150W _{PEP}	_	2.3 -j0.9	_	Ω

^{*} Pulse Test: Pulse Width ≤ 100µs, Duty Cycle ≤ 3%

Fig. Pi TEST CIRCUIT



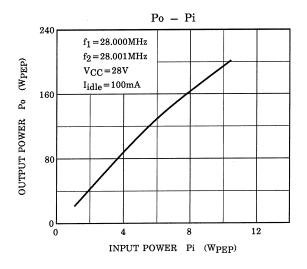
C₁, C₂ : $7\sim150 pF$ L₁ : ϕ 0.8 ENAMEL COATED COPPER WIRE, 14ID, 4T, 4P C₃, C₄ : $7\sim150 pF$ 2KWV L₂ : ϕ 1.2 ENAMEL COATED COPPER WIRE, 14ID, 3 1/2T, 3P

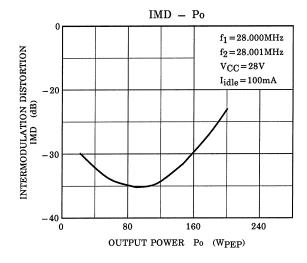
C₅, C₆ : $0.022\mu F$ RFC₁ : $\phi 0.8$ ENAMEL COATED COPPER WIRE, 10ID, 9T C₇ : $47\mu F 10WV$ (Ferrite Core TDK K2)

 $_{\mathrm{C8}}$: 0.04 $\mu\mathrm{F}$ RFC $_{\mathrm{2}}$: ϕ 0.8 ENAMEL COATED COPPER WIRE, 14ID, 20T

C9 : $100 \mu \text{F} 50 \text{WV}$ R₁ : $10 \Omega (1 \text{W})$ R₂ : $2 \Omega (1/2 \text{W})$ R₂ : $10 \Omega (5 \text{W})$

 R_3 : 10Ω (5W) D : 1S1555





CAUTION

These are only typical curves and devices are not necessarily guaranteed at these curves.

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2007-11-01

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20070701-EN GENERAL

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